

Complementary Bias Resistor Transistors

$R_1 = 10\text{ k}\Omega$, $R_2 = \infty\text{ k}\Omega$

NPN and PNP Transistors with Monolithic Bias Resistor Network

MUN5315DW1, NSBC114TPDXV6

This series of digital transistors is designed to replace a single device and its external resistor bias network. The Bias Resistor Transistor (BRT) contains a single transistor with a monolithic bias network consisting of two resistors; a series base resistor and a base-emitter resistor. The BRT eliminates these individual components by integrating them into a single device. The use of a BRT can reduce both system cost and board space.

Features

- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

($T_A = 25^\circ\text{C}$ both polarities Q1 (PNP) and Q2 (NPN), unless otherwise noted)

Symbol	Rating	Max	Unit
V_{CBO}	Collector-Base Voltage	50	Vdc
V_{CEO}	Collector-Emitter Voltage	50	Vdc
I_C	Collector Current – Continuous	100	mAdc
$V_{IN(fwd)}$	Input Forward Voltage	40	Vdc
$V_{IN(rev)}$	Input Reverse Voltage –NPN –PNP	6 5	Vdc

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

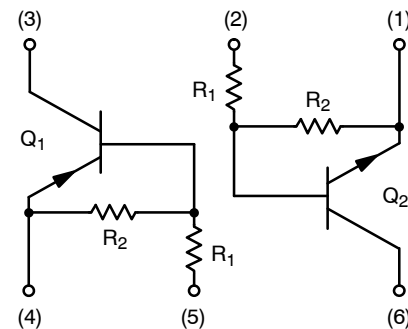


SOT-363
CASE 419B

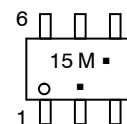


SOT-563
CASE 463A

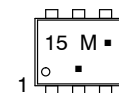
PIN CONNECTIONS



MARKING DIAGRAMS



SOT-363
CASE 419B



SOT-563
CASE 463A

- 15 = Specific Device Code
M = Date Code*
▪ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping†
MUN5315DW1T1G, SMUN5315DW1T1G	SOT-363	3,000 / Tape & Reel
NSBC114TPDXV6T1G	SOT-563	4,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MUN5315DW1, NSBC114TPDXV6

THERMAL CHARACTERISTICS

Symbol	Characteristic	Max	Unit
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MUN5315DW1 (SOT-363) One Junction Heated

P_D	Total Device Dissipation $T_A = 25^\circ\text{C}$ (Note 1)	187	mW
	(Note 2) Derate above 25°C (Note 1)	256 1.5 2.0	mW/ $^\circ\text{C}$
$R_{\theta JA}$	Thermal Resistance, (Note 1) Junction to Ambient (Note 2)	670	$^\circ\text{C}/\text{W}$
		490	

MUN5315DW1 (SOT-363) Both Junction Heated (Note 3)

P_D	Total Device Dissipation $T_A = 25^\circ\text{C}$ (Note 1)	250	mW
	(Note 2) Derate above 25°C (Note 1)	385 2.0 3.0	mW/ $^\circ\text{C}$
$R_{\theta JA}$	Thermal Resistance, (Note 1) Junction to Ambient (Note 2)	493	$^\circ\text{C}/\text{W}$
		325	
$R_{\theta JL}$	Thermal Resistance, (Note 1) Junction to Lead (Note 2)	188	$^\circ\text{C}/\text{W}$
		208	
T_J, T_{stg}	Junction and Storage Temperature Range	-55 to +150	$^\circ\text{C}$

NSBC114TPDXV6 (SOT-563) One Junction Heated

P_D	Total Device Dissipation $T_A = 25^\circ\text{C}$ (Note 1)	357	mW
	Derate above 25°C (Note 1)	2.9	mW/ $^\circ\text{C}$
$R_{\theta JA}$	Thermal Resistance, (Note 1) Junction to Ambient	350	$^\circ\text{C}/\text{W}$

NSBC114TPDXV6 (SOT-563) Both Junction Heated (Note 3)

P_D	Total Device Dissipation $T_A = 25^\circ\text{C}$ (Note 1)	500	mW
	Derate above 25°C (Note 1)	4.0	mW/ $^\circ\text{C}$
$R_{\theta JA}$	Thermal Resistance, (Note 1) Junction to Ambient	250	$^\circ\text{C}/\text{W}$
T_J, T_{stg}	Junction and Storage Temperature Range	-55 to +150	$^\circ\text{C}$

- FR-4 @ Minimum Pad.
- FR-4 @ 1.0 x 1.0 Inch Pad.
- Both junction heated values assume total power is sum of two equally powered channels.

MUN5315DW1, NSBC114TPDXV6

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ both polarities Q_1 (PNP) and Q_2 (NPN), unless otherwise noted)

Symbol	Characteristic	Min	Typ	Max	Unit
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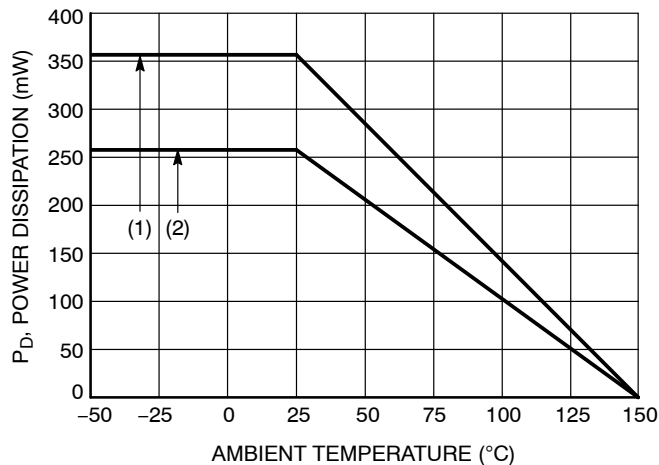
OFF CHARACTERISTICS

I_{CBO}	Collector-Base Cutoff Current ($V_{CB} = 50\text{ V}$, $I_E = 0$)	–	–	100	nAdc
I_{CEO}	Collector-Emitter Cutoff Current ($V_{CE} = 50\text{ V}$, $I_B = 0$)	–	–	500	nAdc
I_{EBO}	Emitter-Base Cutoff Current ($V_{EB} = 6.0\text{ V}$, $I_C = 0$)	–	–	0.9	mAdc
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage ($I_C = 10\text{ }\mu\text{A}$, $I_E = 0$)	50	–	–	Vdc
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage (Note 4) ($I_C = 2.0\text{ mA}$, $I_B = 0$)	50	–	–	Vdc

ON CHARACTERISTICS

h_{FE}	DC Current Gain (Note 4) ($I_C = 5.0\text{ mA}$, $V_{CE} = 10\text{ V}$)	160	350	–	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage (Note 4) ($I_C = 10\text{ mA}$, $I_B = 1.0\text{ mA}$)	–	–	0.25	Vdc
$V_{i(off)}$	Input Voltage (off) ($V_{CE} = 5.0\text{ V}$, $I_C = 100\text{ }\mu\text{A}$) (NPN) ($V_{CE} = 5.0\text{ V}$, $I_C = 100\text{ }\mu\text{A}$) (PNP)	– –	0.6 0.6	– –	Vdc
$V_{i(on)}$	Input Voltage (on) ($V_{CE} = 0.2\text{ V}$, $I_C = 10\text{ mA}$) (NPN) ($V_{CE} = 0.2\text{ V}$, $I_C = 10\text{ mA}$) (PNP)	– –	1.4 1.4	– –	Vdc
V_{OL}	Output Voltage (on) ($V_{CC} = 5.0\text{ V}$, $V_B = 2.5\text{ V}$, $R_L = 1.0\text{ k}\Omega$)	–	–	0.2	Vdc
V_{OH}	Output Voltage (off) ($V_{CC} = 5.0\text{ V}$, $V_B = 0.25\text{ V}$, $R_L = 1.0\text{ k}\Omega$)	4.9	–	–	Vdc
R1	Input Resistor	7.0	10	13	k Ω
R_1/R_2	Resistor Ratio	–	–	–	

4. Pulsed Condition: Pulse Width = 300 msec, Duty Cycle $\leq 2\%$.



(1) SOT-363; 1.0 x 1.0 inch Pad
(2) SOT-563; Minimum Pad

Figure 1. Derating Curve

TYPICAL CHARACTERISTICS – NPN TRANSISTOR
MUN5315DW1, NSBC114TPDXV6

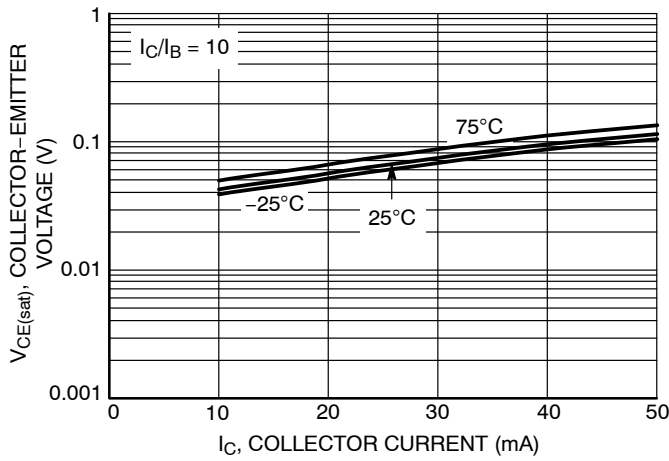


Figure 2. $V_{CE(sat)}$ vs. I_C

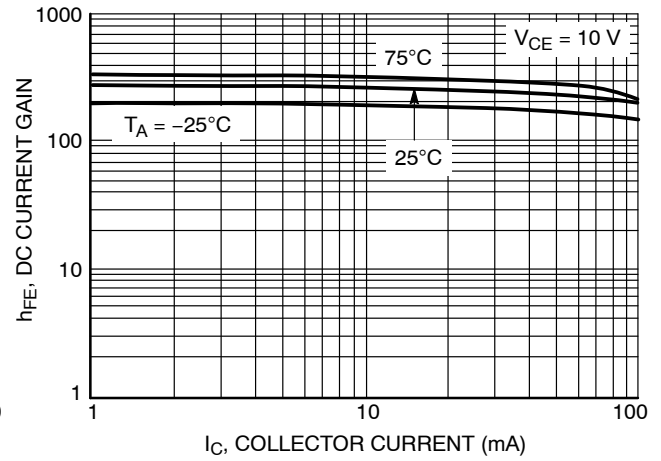


Figure 3. DC Current Gain

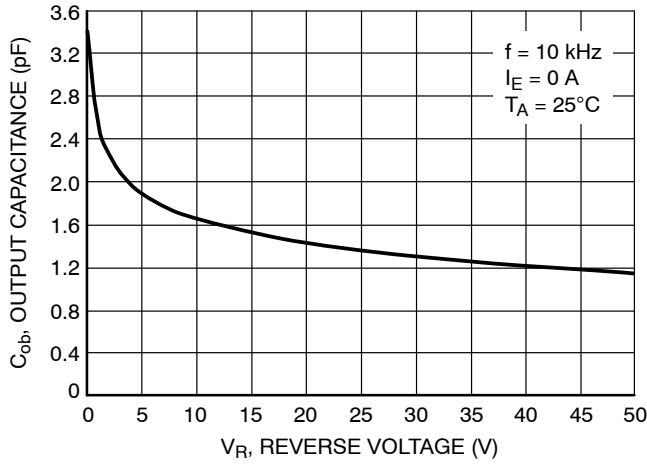


Figure 4. Output Capacitance

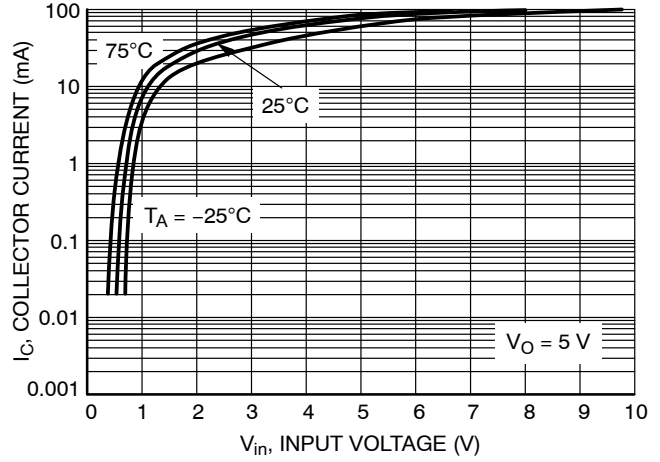


Figure 5. Output Current vs. Input Voltage

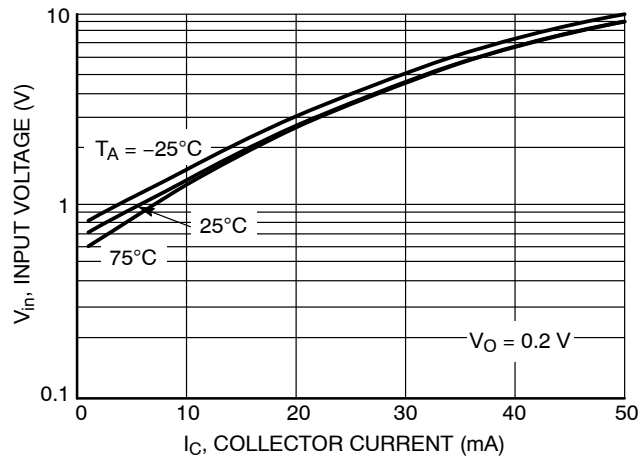


Figure 6. Input Voltage vs. Output Current

TYPICAL CHARACTERISTICS – PNP TRANSISTOR
MUN5315DW1, NSBC114TPDXV6

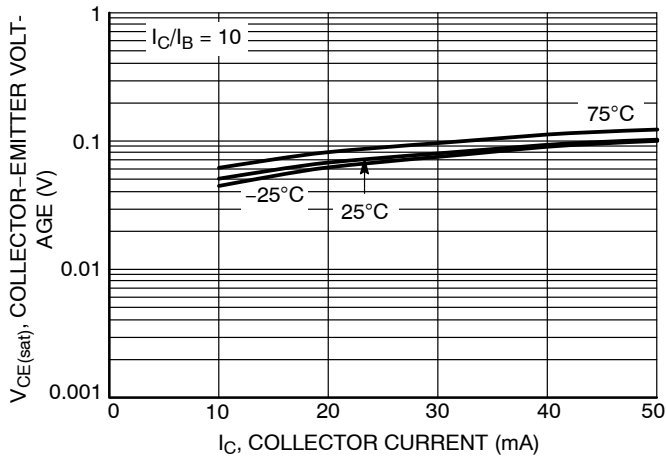


Figure 7. $V_{CE(sat)}$ vs. I_C

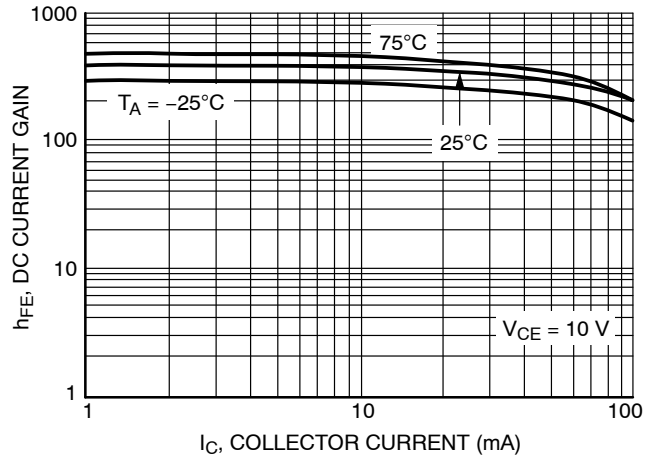


Figure 8. DC Current Gain

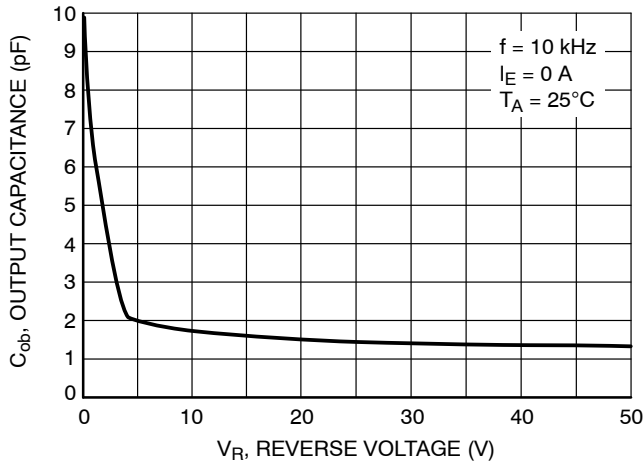


Figure 9. Output Capacitance

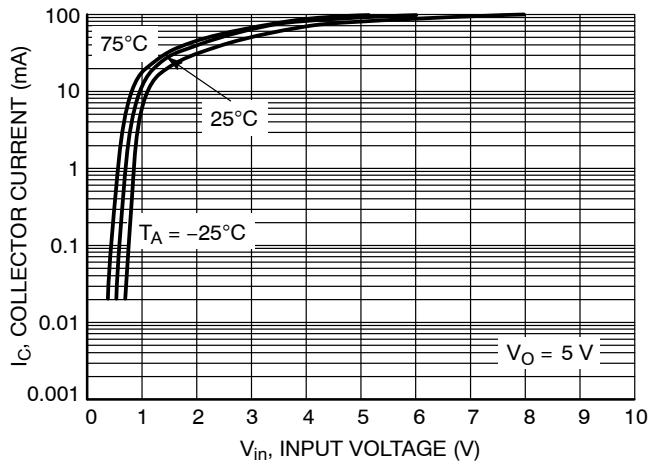


Figure 10. Output Current vs. Input Voltage

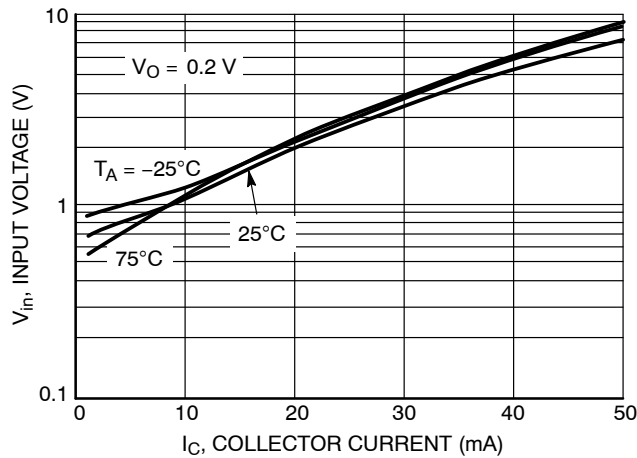


Figure 11. Input Voltage vs. Output Current



SC-88 2.00x1.25x0.90, 0.65P
CASE 419B-02
ISSUE Z

DATE 18 APR 2024

NOTES:

1. DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5-2018.
2. ALL DIMENSION ARE IN MILLIMETERS.
3. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.20 PER END.
4. DIMENSIONS D AND E1 AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY AND DATUM H.
5. DATUMS A AND B ARE DETERMINED AT DATUM H.
6. DIMENSIONS b AND c APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN 0.08 AND 0.15 FROM THE TIP.
7. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 TOTAL IN EXCESS OF DIMENSION b AT MAXIMUM MATERIAL CONDITION. THE DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OF THE FOOT.

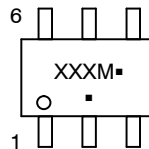


DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	---	---	1.10
A1	0.00	---	0.10
A2	0.70	0.90	1.00
b	0.15	0.20	0.25
c	0.08	0.15	0.22
D	2.00 BSC		
E	2.10 BSC		
E1	1.25 BSC		
e	0.65 BSC		
L	0.26	0.36	0.46
L2	0.15 BSC		
aaa	0.15		
bbb	0.30		
ccc	0.10		
ddd	0.10		



* FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ONSEMI SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

GENERIC
MARKING DIAGRAM*



XXX = Specific Device Code
M = Date Code*
▪ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or position may vary depending upon manufacturing location.

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

STYLES ON PAGE 2

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SC-88 2.00x1.25x0.90, 0.65P
CASE 419B-02
ISSUE Z

DATE 18 APR 2024

STYLE 1: PIN 1. EMITTER 2 2. BASE 2 3. COLLECTOR 1 4. EMITTER 1 5. BASE 1 6. COLLECTOR 2	STYLE 2: CANCELLED	STYLE 3: CANCELLED	STYLE 4: PIN 1. CATHODE 2. CATHODE 3. COLLECTOR 4. EMITTER 5. BASE 6. ANODE	STYLE 5: PIN 1. ANODE 2. ANODE 3. COLLECTOR 4. EMITTER 5. BASE 6. CATHODE	STYLE 6: PIN 1. ANODE 2 2. N/C 3. CATHODE 1 4. ANODE 1 5. N/C 6. CATHODE 2
STYLE 7: PIN 1. SOURCE 2 2. DRAIN 2 3. GATE 1 4. SOURCE 1 5. DRAIN 1 6. GATE 2	STYLE 8: CANCELLED	STYLE 9: PIN 1. EMITTER 2 2. EMITTER 1 3. COLLECTOR 1 4. BASE 1 5. BASE 2 6. COLLECTOR 2	STYLE 10: PIN 1. SOURCE 2 2. SOURCE 1 3. GATE 1 4. DRAIN 1 5. DRAIN 2 6. GATE 2	STYLE 11: PIN 1. CATHODE 2 2. CATHODE 2 3. ANODE 1 4. CATHODE 1 5. CATHODE 1 6. ANODE 2	STYLE 12: PIN 1. ANODE 2 2. ANODE 2 3. CATHODE 1 4. ANODE 1 5. ANODE 1 6. CATHODE 2
STYLE 13: PIN 1. ANODE 2. N/C 3. COLLECTOR 4. EMITTER 5. BASE 6. CATHODE	STYLE 14: PIN 1. VREF 2. GND 3. GND 4. IOUT 5. VEN 6. VCC	STYLE 15: PIN 1. ANODE 1 2. ANODE 2 3. ANODE 3 4. CATHODE 3 5. CATHODE 2 6. CATHODE 1	STYLE 16: PIN 1. BASE 1 2. EMITTER 2 3. COLLECTOR 2 4. BASE 2 5. EMITTER 1 6. COLLECTOR 1	STYLE 17: PIN 1. BASE 1 2. EMITTER 1 3. COLLECTOR 2 4. BASE 2 5. EMITTER 2 6. COLLECTOR 1	STYLE 18: PIN 1. VIN1 2. VCC 3. VOUT2 4. VIN2 5. GND 6. VOUT1
STYLE 19: PIN 1. I OUT 2. GND 3. GND 4. V CC 5. V EN 6. V REF	STYLE 20: PIN 1. COLLECTOR 2. COLLECTOR 3. BASE 4. EMITTER 5. COLLECTOR 6. COLLECTOR	STYLE 21: PIN 1. ANODE 1 2. N/C 3. ANODE 2 4. CATHODE 2 5. N/C 6. CATHODE 1	STYLE 22: PIN 1. D1 (i) 2. GND 3. D2 (i) 4. D2 (c) 5. VBUS 6. D1 (c)	STYLE 23: PIN 1. Vn 2. CH1 3. Vp 4. N/C 5. CH2 6. N/C	STYLE 24: PIN 1. CATHODE 2. ANODE 3. CATHODE 4. CATHODE 5. CATHODE 6. CATHODE
STYLE 25: PIN 1. BASE 1 2. CATHODE 3. COLLECTOR 2 4. BASE 2 5. EMITTER 6. COLLECTOR 1	STYLE 26: PIN 1. SOURCE 1 2. GATE 1 3. DRAIN 2 4. SOURCE 2 5. GATE 2 6. DRAIN 1	STYLE 27: PIN 1. BASE 2 2. BASE 1 3. COLLECTOR 1 4. EMITTER 1 5. EMITTER 2 6. COLLECTOR 2	STYLE 28: PIN 1. DRAIN 2. DRAIN 3. GATE 4. SOURCE 5. DRAIN 6. DRAIN	STYLE 29: PIN 1. ANODE 2. ANODE 3. COLLECTOR 4. EMITTER 5. BASE/ANODE 6. CATHODE	STYLE 30: PIN 1. SOURCE 1 2. DRAIN 2 3. DRAIN 2 4. SOURCE 2 5. GATE 1 6. DRAIN 1

Note: Please refer to datasheet for style callout. If style type is not called out in the datasheet refer to the device datasheet pinout or pin assignment.

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SOT-563-6 1.60x1.20x0.55, 0.50P
CASE 463A
ISSUE J

DATE 15 FEB 2024

NOTES:

1. DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5-2018.
2. ALL DIMENSION ARE IN MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.



DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.50	0.55	0.60
b	0.17	0.22	0.27
c	0.08	0.13	0.18
D	1.50	1.60	1.70
E	1.10	1.20	1.30
e	0.50 BSC		
H	1.50	1.60	1.70
L	0.10	0.20	0.30



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STYLE 1:
PIN 1. EMITTER 1
2. BASE 1
3. COLLECTOR 2
4. EMITTER 2
5. BASE 2
6. COLLECTOR 1

STYLE 2:
PIN 1. EMITTER 1
2. EMITTER 2
3. BASE 2
4. COLLECTOR 2
5. BASE 1
6. COLLECTOR 1

STYLE 3:
PIN 1. CATHODE 1
2. CATHODE 1
3. ANODE/ANODE 2
4. CATHODE 2
5. CATHODE 2
6. ANODE/ANODE 1

STYLE 4:
PIN 1. COLLECTOR
2. COLLECTOR
3. BASE
4. EMITTER
5. COLLECTOR
6. COLLECTOR

STYLE 5:
PIN 1. CATHODE
2. CATHODE
3. ANODE
4. ANODE
5. CATHODE
6. CATHODE

STYLE 6:
PIN 1. CATHODE
2. ANODE
3. CATHODE
4. CATHODE
5. CATHODE
6. CATHODE

STYLE 7:
PIN 1. CATHODE
2. ANODE
3. CATHODE
4. CATHODE
5. ANODE
6. CATHODE

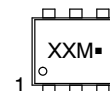
STYLE 8:
PIN 1. DRAIN
2. DRAIN
3. GATE
4. SOURCE
5. DRAIN
6. DRAIN

STYLE 9:
PIN 1. SOURCE 1
2. GATE 1
3. DRAIN 2
4. SOURCE 2
5. GATE 2
6. DRAIN 1

STYLE 10:
PIN 1. CATHODE 1
2. N/C
3. CATHODE 2
4. ANODE 2
5. N/C
6. ANODE 1

STYLE 11:
PIN 1. EMITTER 2
2. BASE 2
3. COLLECTOR 1
4. EMITTER 1
5. BASE 1
6. COLLECTOR 2

**GENERIC
MARKING DIAGRAM***



XX = Specific Device Code
M = Month Code
▪ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

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